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Understanding <u>Embedded - FPGAs (Field Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	72
Number of Logic Elements/Cells	576
Total RAM Bits	6144
Number of I/O	134
Number of Gates	31000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k10qc208-3

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Application	Resourc	es Used		Performance				
	LEs	EABs	-1 Speed Grade	-2 Speed Grade	-3 Speed Grade			
16-bit loadable counter	16	0	285	250	200	MHz		
16-bit accumulator	16	0	285	250	200	MHz		
16-to-1 multiplexer (1)	10	0	3.5	4.9	7.0	ns		
16-bit multiplier with 3-stage pipeline (2)	592	0	156	131	93	MHz		
256 × 16 RAM read cycle speed (2)	0	1	196	154	118	MHz		
256 × 16 RAM write cycle	0	1	185	143	106	MHz		

Notes:

- (1) This application uses combinatorial inputs and outputs.
- (2) This application uses registered inputs and outputs.

Table 6 shows FLEX 10KE performance for more complex designs. These designs are available as Altera MegaCore $^{\circ}$ functions.

Table 6. FLEX 10KE Performance for Complex Designs									
Application	LEs Used		Performance		Units				
		-1 Speed Grade	-2 Speed Grade	-3 Speed Grade					
8-bit, 16-tap parallel finite impulse response (FIR) filter	597	192	156	116	MSPS				
8-bit, 512-point fast Fourier	1,854	23.4	28.7	38.9	μ s (1)				
transform (FFT) function		113	92	68	MHz				
a16450 universal asynchronous receiver/transmitter (UART)	342	36	28	20.5	MHz				

Note:

(1) These values are for calculation time. Calculation time = number of clocks required / f_{max} . Number of clocks required = ceiling [log 2 (points)/2] × [points +14 + ceiling]

Similar to the FLEX 10KE architecture, embedded gate arrays are the fastest-growing segment of the gate array market. As with standard gate arrays, embedded gate arrays implement general logic in a conventional "sea-of-gates" architecture. Additionally, embedded gate arrays have dedicated die areas for implementing large, specialized functions. By embedding functions in silicon, embedded gate arrays reduce die area and increase speed when compared to standard gate arrays. While embedded megafunctions typically cannot be customized, FLEX 10KE devices are programmable, providing the designer with full control over embedded megafunctions and general logic, while facilitating iterative design changes during debugging.

Each FLEX 10KE device contains an embedded array and a logic array. The embedded array is used to implement a variety of memory functions or complex logic functions, such as digital signal processing (DSP), wide data-path manipulation, microcontroller applications, and data-transformation functions. The logic array performs the same function as the sea-of-gates in the gate array and is used to implement general logic such as counters, adders, state machines, and multiplexers. The combination of embedded and logic arrays provides the high performance and high density of embedded gate arrays, enabling designers to implement an entire system on a single device.

FLEX 10KE devices are configured at system power-up with data stored in an Altera serial configuration device or provided by a system controller. Altera offers the EPC1, EPC2, and EPC16 configuration devices, which configure FLEX 10KE devices via a serial data stream. Configuration data can also be downloaded from system RAM or via the Altera BitBlasterTM, ByteBlasterMVTM, or MasterBlaster download cables. After a FLEX 10KE device has been configured, it can be reconfigured in-circuit by resetting the device and loading new data. Because reconfiguration requires less than 85 ms, real-time changes can be made during system operation.

FLEX 10KE devices contain an interface that permits microprocessors to configure FLEX 10KE devices serially or in-parallel, and synchronously or asynchronously. The interface also enables microprocessors to treat a FLEX 10KE device as memory and configure it by writing to a virtual memory location, making it easy to reconfigure the device.

Embedded Array Block

The EAB is a flexible block of RAM, with registers on the input and output ports, that is used to implement common gate array megafunctions. Because it is large and flexible, the EAB is suitable for functions such as multipliers, vector scalars, and error correction circuits. These functions can be combined in applications such as digital filters and microcontrollers.

Logic functions are implemented by programming the EAB with a read-only pattern during configuration, thereby creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement any function with 8 inputs and 16 outputs. Parameterized functions such as LPM functions can take advantage of the EAB automatically.

The FLEX 10KE EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These small FPGA RAM blocks must be connected together to make RAM blocks of manageable size. The RAM blocks are connected together using multiplexers implemented with more logic blocks. These extra multiplexers cause extra delay, which slows down the RAM block. FPGA RAM blocks are also prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

The FLEX 10KE enhanced EAB adds dual-port capability to the existing EAB structure. The dual-port structure is ideal for FIFO buffers with one or two clocks. The FLEX 10KE EAB can also support up to 16-bit-wide RAM blocks and is backward-compatible with any design containing FLEX 10K EABs. The FLEX 10KE EAB can act in dual-port or single-port mode. When in dual-port mode, separate clocks may be used for EAB read and write sections, which allows the EAB to be written and read at different rates. It also has separate synchronous clock enable signals for the EAB read and write sections, which allow independent control of these sections.

The EAB can also be used for bidirectional, dual-port memory applications where two ports read or write simultaneously. To implement this type of dual-port memory, two EABs are used to support two simultaneous read or writes.

Alternatively, one clock and clock enable can be used to control the input registers of the EAB, while a different clock and clock enable control the output registers (see Figure 2).

Dedicated Inputs & Global Signals **Dedicated Clocks** Row Interconnect RAM/ROM 256 × 16 512 × 8 data[] 2.048 × 2 ENA FNA rdaddress[] EAB Local ENA Interconnect (2) wraddress[] 4, 8, 16, 32 FΝΔ rden wren outclocken Write Enable inclocken Multiplexers allow read address and read inclock enable registers to be clocked by inclock or outclock outclock signals.

Figure 2. FLEX 10KE Device in Dual-Port RAM Mode Notes (1)

Notes:

(1) All registers can be asynchronously cleared by EAB local interconnect signals, global signals, or the chip-wide reset.

Column Interconnect

(2) EPF10K30E and EPF10K50E devices have 88 EAB local interconnect channels; EPF10K100E, EPF10K130E, and EPF10K200E devices have 104 EAB local interconnect channels.

The programmable flipflop in the LE can be configured for D, T, JK, or SR operation. The clock, clear, and preset control signals on the flipflop can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinatorial functions, the flipflop is bypassed and the output of the LUT drives the output of the LE.

The LE has two outputs that drive the interconnect: one drives the local interconnect and the other drives either the row or column FastTrack Interconnect routing structure. The two outputs can be controlled independently. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, can improve LE utilization because the register and the LUT can be used for unrelated functions.

The FLEX 10KE architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. The carry chain supports high-speed counters and adders and the cascade chain implements wide-input functions with minimum delay. Carry and cascade chains connect all LEs in a LAB as well as all LABs in the same row. Intensive use of carry and cascade chains can reduce routing flexibility. Therefore, the use of these chains should be limited to speed-critical portions of a design.

Carry Chain

The carry chain provides a very fast (as low as 0.2 ns) carry-forward function between LEs. The carry-in signal from a lower-order bit drives forward into the higher-order bit via the carry chain, and feeds into both the LUT and the next portion of the carry chain. This feature allows the FLEX 10KE architecture to implement high-speed counters, adders, and comparators of arbitrary width efficiently. Carry chain logic can be created automatically by the Altera Compiler during design processing, or manually by the designer during design entry. Parameterized functions such as LPM and DesignWare functions automatically take advantage of carry chains.

Carry chains longer than eight LEs are automatically implemented by linking LABs together. For enhanced fitting, a long carry chain skips alternate LABs in a row. A carry chain longer than one LAB skips either from even-numbered LAB to even-numbered LAB, or from odd-numbered LAB to odd-numbered LAB. For example, the last LE of the first LAB in a row carries to the first LE of the third LAB in the row. The carry chain does not cross the EAB at the middle of the row. For instance, in the EPF10K50E device, the carry chain stops at the eighteenth LAB and a new one begins at the nineteenth LAB.

PCI Pull-Up Clamping Diode Option

FLEX 10KE devices have a pull-up clamping diode on every I/O, dedicated input, and dedicated clock pin. PCI clamping diodes clamp the signal to the $V_{\rm CCIO}$ value and are required for 3.3-V PCI compliance. Clamping diodes can also be used to limit overshoot in other systems.

Clamping diodes are controlled on a pin-by-pin basis. When $V_{\rm CCIO}$ is 3.3 V, a pin that has the clamping diode option turned on can be driven by a 2.5-V or 3.3-V signal, but not a 5.0-V signal. When $V_{\rm CCIO}$ is 2.5 V, a pin that has the clamping diode option turned on can be driven by a 2.5-V signal, but not a 3.3-V or 5.0-V signal. Additionally, a clamping diode can be activated for a subset of pins, which would allow a device to bridge between a 3.3-V PCI bus and a 5.0-V device.

Slew-Rate Control

The output buffer in each IOE has an adjustable output slew rate that can be configured for low-noise or high-speed performance. A slower slew rate reduces system noise and adds a maximum delay of 4.3 ns. The fast slew rate should be used for speed-critical outputs in systems that are adequately protected against noise. Designers can specify the slew rate pin-by-pin or assign a default slew rate to all pins on a device-wide basis. The slow slew rate setting affects the falling edge of the output.

Open-Drain Output Option

FLEX 10KE devices provide an optional open-drain output (electrically equivalent to open-collector output) for each I/O pin. This open-drain output enables the device to provide system-level control signals (e.g., interrupt and write enable signals) that can be asserted by any of several devices. It can also provide an additional wired- \mathbb{QR} plane.

MultiVolt I/O Interface

The FLEX 10KE device architecture supports the MultiVolt I/O interface feature, which allows FLEX 10KE devices in all packages to interface with systems of differing supply voltages. These devices have one set of V_{CC} pins for internal operation and input buffers (VCCINT), and another set for I/O output drivers (VCCIO).

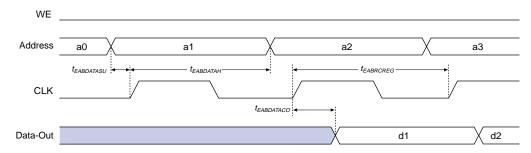
3 Timing Macroparameters Note (1), (6)	
Parameter	Conditions
EAB address access delay	
EAB asynchronous read cycle time	
EAB synchronous read cycle time	
EAB write pulse width	
EAB asynchronous write cycle time	
EAB synchronous write cycle time	
EAB data-in to data-out valid delay	
EAB clock-to-output delay when using output registers	
EAB data/address setup time before clock when using input register	
EAB data/address hold time after clock when using input register	
EAB WE setup time before clock when using input register	
EAB WE hold time after clock when using input register	
EAB data setup time before falling edge of write pulse when not using input registers	
EAB data hold time after falling edge of write pulse when not using input registers	
EAB address setup time before rising edge of write pulse when not using input registers	
EAB address hold time after falling edge of write pulse when not using input registers	
EAB write enable to data output valid delay	
	Parameter EAB address access delay EAB asynchronous read cycle time EAB synchronous read cycle time EAB write pulse width EAB asynchronous write cycle time EAB synchronous write cycle time EAB data-in to data-out valid delay EAB clock-to-output delay when using output registers EAB data/address setup time before clock when using input register EAB we setup time before clock when using input register EAB we hold time after clock when using input register EAB data setup time before falling edge of write pulse when not using input registers EAB data hold time after falling edge of write pulse when not using input registers EAB address setup time before rising edge of write pulse when not using input registers EAB address setup time before rising edge of write pulse when not using input registers EAB address hold time after falling edge of write pulse when not using input registers

Table 28. Inte	rconnect Timing Microparameters Note (1)						
Symbol	Symbol Parameter						
t _{DIN2IOE}	Delay from dedicated input pin to IOE control input	(7)					
t _{DIN2LE}	Delay from dedicated input pin to LE or EAB control input	(7)					
t _{DCLK2IOE}	Delay from dedicated clock pin to IOE clock	(7)					
t _{DCLK2LE}	Delay from dedicated clock pin to LE or EAB clock	(7)					
t _{DIN2DATA}	Delay from dedicated input or clock to LE or EAB data	(7)					
t _{SAMELAB}	Routing delay for an LE driving another LE in the same LAB						
t _{SAMEROW}	Routing delay for a row IOE, LE, or EAB driving a row IOE, LE, or EAB in the same row	(7)					
t _{SAME} COLUMN	Routing delay for an LE driving an IOE in the same column	(7)					
t _{DIFFROW}	Routing delay for a column IOE, LE, or EAB driving an LE or EAB in a different row	(7)					
t _{TWOROWS}	Routing delay for a row IOE or EAB driving an LE or EAB in a different row	(7)					
t _{LEPERIPH}	Routing delay for an LE driving a control signal of an IOE via the peripheral control bus	(7)					
t _{LABCARRY}	Routing delay for the carry-out signal of an LE driving the carry-in signal of a different LE in a different LAB						
t _{LABCASC}	Routing delay for the cascade-out signal of an LE driving the cascade-in signal of a different LE in a different LAB						

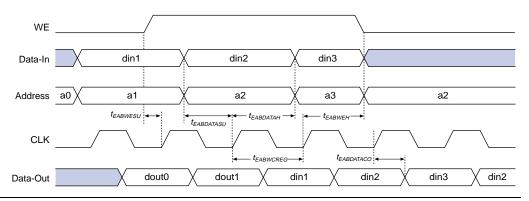
Table 29. Exte	ernal Timing Parameters	
Symbol	Parameter	Conditions
t _{DRR}	Register-to-register delay via four LEs, three row interconnects, and four local interconnects	(8)
t _{INSU}	Setup time with global clock at IOE register	(9)
t _{INH}	Hold time with global clock at IOE register	(9)
tоитсо	Clock-to-output delay with global clock at IOE register	(9)
t _{PCISU}	Setup time with global clock for registers used in PCI designs	(9),(10)
t _{PCIH}	Hold time with global clock for registers used in PCI designs	(9),(10)
t _{PCICO}	Clock-to-output delay with global clock for registers used in PCI designs	(9),(10)

Figure 30. EAB Synchronous Timing Waveforms

EAB Synchronous Read



EAB Synchronous Write (EAB Output Registers Used)



Tables 31 through 37 show EPF10K30E device internal and external timing parameters.

Table 31. EPF10	K30E Device	LE Timing N	1icroparame	ters (Part 1	of 2) No	ote (1)	
Symbol	-1 Spec	-1 Speed Grade		-2 Speed Grade		d Grade	Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.7		0.8		1.1	ns
t _{CLUT}		0.5		0.6		0.8	ns
t _{RLUT}		0.6		0.7		1.0	ns
t _{PACKED}		0.3		0.4		0.5	ns
t_{EN}		0.6		0.8		1.0	ns
t _{CICO}		0.1		0.1		0.2	ns
t _{CGEN}		0.4		0.5		0.7	ns

Table 31. EPF10	K30E Device	LE Timing N	<i>Nicroparame</i>	ters (Part 2	? of 2) No	ote (1)	
Symbol	-1 Spee	-1 Speed Grade		-2 Speed Grade		ed Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{CGENR}		0.1		0.1		0.2	ns
t _{CASC}		0.6		0.8		1.0	ns
$t_{\mathbb{C}}$		0.0		0.0		0.0	ns
t_{CO}		0.3		0.4		0.5	ns
t _{COMB}		0.4		0.4		0.6	ns
t_{SU}	0.4		0.6		0.6		ns
t_H	0.7		1.0		1.3		ns
t _{PRE}		0.8		0.9		1.2	ns
t _{CLR}		0.8		0.9		1.2	ns
t _{CH}	2.0		2.5		2.5		ns
t_{CL}	2.0		2.5		2.5		ns

Table 32. EPF10K30E Device IOE Timing Microparameters Note (1)								
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Spec	ed Grade	Unit	
	Min	Max	Min	Max	Min	Max		
t _{IOD}		2.4		2.8		3.8	ns	
t _{IOC}		0.3		0.4		0.5	ns	
t _{IOCO}		1.0		1.1		1.6	ns	
t _{IOCOMB}		0.0		0.0		0.0	ns	
t _{IOSU}	1.2		1.4		1.9		ns	
t _{IOH}	0.3		0.4		0.5		ns	
t _{IOCLR}		1.0		1.1		1.6	ns	
t _{OD1}		1.9		2.3		3.0	ns	
t _{OD2}		1.4		1.8		2.5	ns	
t _{OD3}		4.4		5.2		7.0	ns	
t_{XZ}		2.7		3.1		4.3	ns	
t_{ZX1}		2.7		3.1		4.3	ns	
t_{ZX2}		2.2		2.6		3.8	ns	
t_{ZX3}		5.2		6.0		8.3	ns	
t _{INREG}		3.4		4.1		5.5	ns	
t _{IOFD}		0.8		1.3		2.4	ns	
t _{INCOMB}		0.8		1.3		2.4	ns	

Symbol	-1 Spee	d Grade	-2 Speed Grade		-3 Spee	ed Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{DIN2IOE}		1.8		2.4		2.9	ns
t _{DIN2LE}		1.5		1.8		2.4	ns
t _{DIN2DATA}		1.5		1.8		2.2	ns
t _{DCLK2IOE}		2.2		2.6		3.0	ns
t _{DCLK2LE}		1.5		1.8		2.4	ns
t _{SAMELAB}		0.1		0.2		0.3	ns
t _{SAMEROW}		2.0		2.4		2.7	ns
t _{SAME} COLUMN		0.7		1.0		0.8	ns
t _{DIFFROW}		2.7		3.4		3.5	ns
t _{TWOROWS}		4.7		5.8		6.2	ns
t _{LEPERIPH}		2.7		3.4		3.8	ns
t _{LABCARRY}		0.3		0.4		0.5	ns
t _{LABCASC}		0.8		0.8		1.1	ns

Symbol	-1 Spec	-1 Speed Grade		-2 Speed Grade		d Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{DRR}		8.0		9.5		12.5	ns
t _{INSU} (3)	2.1		2.5		3.9		ns
t _{INH} (3)	0.0		0.0		0.0		ns
t _{оитсо} (3)	2.0	4.9	2.0	5.9	2.0	7.6	ns
t _{INSU} (4)	1.1		1.5		-		ns
t _{INH} (4)	0.0		0.0		-		ns
^t оитсо	0.5	3.9	0.5	4.9	-	-	ns
t _{PCISU}	3.0		4.2		-		ns
рсін	0.0		0.0		-		ns
t _{PCICO}	2.0	6.0	2.0	7.5	_	_	ns

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSUBIDIR} (3)	2.8		3.9		5.2		ns
t _{INHBIDIR} (3)	0.0		0.0		0.0		ns
t _{INSUBIDIR} (4)	3.8		4.9		-		ns
t _{INHBIDIR} (4)	0.0		0.0		-		ns
toutcobidir (3)	2.0	4.9	2.0	5.9	2.0	7.6	ns
t _{XZBIDIR} (3)		6.1		7.5		9.7	ns
t _{ZXBIDIR} (3)		6.1		7.5		9.7	ns
toutcobidir (4)	0.5	3.9	0.5	4.9	-	-	ns
t _{XZBIDIR} (4)		5.1		6.5		-	ns
t _{ZXBIDIR} (4)		5.1		6.5		_	ns

Notes to tables:

- (1) All timing parameters are described in Tables 24 through 30 in this data sheet.
- (2) These parameters are specified by characterization.
- (3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
- (4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Tables 38 through 44 show EPF10K50E device internal and external timing parameters.

Table 38. EPF10I	K50E Device	LE Timing N	/licroparame	eters (Part 1	of 2) No	ote (1)	
Symbol	-1 Spee	ed Grade	-2 Spee	d Grade	-3 Spee	ed Grade	Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.6		0.9		1.3	ns
t _{CLUT}		0.5		0.6		0.8	ns
t _{RLUT}		0.7		0.8		1.1	ns
t _{PACKED}		0.4		0.5		0.6	ns
t _{EN}		0.6		0.7		0.9	ns
t _{CICO}		0.2		0.2		0.3	ns
t _{CGEN}		0.5		0.5		0.8	ns
t _{CGENR}		0.2		0.2		0.3	ns
t _{CASC}		0.8		1.0		1.4	ns
$t_{\rm C}$		0.5		0.6		0.8	ns
t_{CO}		0.7		0.7		0.9	ns
t _{COMB}		0.5		0.6		0.8	ns
t_{SU}	0.7		0.7		0.8		ns

Table 38. EPF10K	50E Device	LE Timing M	licroparame	ters (Part 2	of 2) No	te (1)	
Symbol	-1 Spee	ed Grade -2 Speed		ed Grade -3 Speed		d Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _H	0.9		1.0		1.4		ns
t _{PRE}		0.5		0.6		0.8	ns
t _{CLR}		0.5		0.6		0.8	ns
t _{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 39. EPF10	K50E Device	IOE Timing	Microparam	neters No	te (1)		
Symbol	-1 Speed Grade		-2 Spee	-2 Speed Grade		ed Grade	Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		2.2		2.4		3.3	ns
t _{IOC}		0.3		0.3		0.5	ns
t_{IOCO}		1.0		1.0		1.4	ns
t _{IOCOMB}		0.0		0.0		0.2	ns
t _{IOSU}	1.0		1.2		1.7		ns
t _{IOH}	0.3		0.3		0.5		ns
t _{IOCLR}		0.9		1.0		1.4	ns
t _{OD1}		0.8		0.9		1.2	ns
t _{OD2}		0.3		0.4		0.7	ns
t _{OD3}		3.0		3.5		3.5	ns
t_{XZ}		1.4		1.7		2.3	ns
t_{ZX1}		1.4		1.7		2.3	ns
t_{ZX2}		0.9		1.2		1.8	ns
t _{ZX3}		3.6		4.3		4.6	ns
t _{INREG}		4.9		5.8		7.8	ns
t _{IOFD}		2.8		3.3		4.5	ns
t _{INCOMB}		2.8	_	3.3	_	4.5	ns

Symbol	-1 Spee	d Grade	-2 Spee	d Grade	-3 Spee	d Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{CGENR}		0.1		0.1		0.2	ns
t _{CASC}		0.6		0.9		1.2	ns
t _C		0.8		1.0		1.4	ns
t _{CO}		0.6		0.8		1.1	ns
t _{COMB}		0.4		0.5		0.7	ns
t _{SU}	0.4		0.6		0.7		ns
t _H	0.5		0.7		0.9		ns
t _{PRE}		0.8		1.0		1.4	ns
t _{CLR}		0.8		1.0		1.4	ns
t _{CH}	1.5		2.0		2.5		ns
t_{CL}	1.5		2.0		2.5		ns

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.7		2.0		2.6	ns
t _{IOC}		0.0		0.0		0.0	ns
t_{IOCO}		1.4		1.6		2.1	ns
t_{IOCOMB}		0.5		0.7		0.9	ns
t _{IOSU}	0.8		1.0		1.3		ns
t_{IOH}	0.7		0.9		1.2		ns
t _{IOCLR}		0.5		0.7		0.9	ns
t_{OD1}		3.0		4.2		5.6	ns
t_{OD2}		3.0		4.2		5.6	ns
t_{OD3}		4.0		5.5		7.3	ns
t_{XZ}		3.5		4.6		6.1	ns
t _{ZX1}		3.5		4.6		6.1	ns
t _{ZX2}		3.5		4.6		6.1	ns
t _{ZX3}		4.5		5.9		7.8	ns
t _{INREG}		2.0		2.6		3.5	ns
t _{IOFD}		0.5		0.8		1.2	ns
t _{INCOMB}		0.5		0.8		1.2	ns

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{EABDATA1}		1.5		2.0		2.6	ns
t _{EABDATA1}		0.0		0.0		0.0	ns
t _{EABWE1}		1.5		2.0		2.6	ns
t _{EABWE2}		0.3		0.4		0.5	ns
t _{EABRE1}		0.3		0.4		0.5	ns
t _{EABRE2}		0.0		0.0		0.0	ns
t _{EABCLK}		0.0		0.0		0.0	ns
t _{EABCO}		0.3		0.4		0.5	ns
t _{EABBYPASS}		0.1		0.1		0.2	ns
t _{EABSU}	0.8		1.0		1.4		ns
t _{EABH}	0.1		0.1		0.2		ns
t _{EABCLR}	0.3		0.4		0.5		ns
t_{AA}		4.0		5.1		6.6	ns
t_{WP}	2.7		3.5		4.7		ns
t_{RP}	1.0		1.3		1.7		ns
t _{WDSU}	1.0		1.3		1.7		ns
t _{WDH}	0.2		0.2		0.3		ns
t _{WASU}	1.6		2.1		2.8		ns
t _{WAH}	1.6		2.1		2.8		ns
t _{RASU}	3.0		3.9		5.2		ns
t _{RAH}	0.1		0.1		0.2		ns
t _{WO}		1.5		2.0		2.6	ns
t _{DD}		1.5		2.0		2.6	ns
t _{EABOUT}		0.2		0.3		0.3	ns
t _{EABCH}	1.5		2.0		2.5		ns
t _{EABCL}	2.7		3.5		4.7		ns

Table 48. EPF10K	100E Device	EAB Interna	al Timing M	acroparame	ters (Part 1	of 2) No	nte (1)
Symbol	-1 Spee	d Grade	-2 Spee	d Grade	-3 Spee	d Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{EABAA}		5.9		7.6		9.9	ns
t _{EABRCOMB}	5.9		7.6		9.9		ns
t _{EABRCREG}	5.1		6.5		8.5		ns
t_{EABWP}	2.7		3.5		4.7		ns

Table 54. EPF10	K130E Device	EAB Interna	al Micropara	ameters (Pa	art 2 of 2)	Note (1)	
Symbol	-1 Spee	d Grade	-2 Spee	d Grade	-3 Spee	d Grade	Unit
	Min	Max	Min	Max	Min	Max	
t_{DD}		1.5		2.0		2.6	ns
t _{EABOUT}		0.2		0.3		0.3	ns
t _{EABCH}	1.5		2.0		2.5		ns
t _{EABCL}	2.7		3.5		4.7		ns

Table 55. EPF10	K130E Device	e EAB Intern	al Timing M	lacroparame	ters Note	e (1)	
Symbol	-1 Speed Grade		-2 Spee	-2 Speed Grade		ed Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{EABAA}		5.9		7.5		9.9	ns
t _{EABRCOMB}	5.9		7.5		9.9		ns
t _{EABRCREG}	5.1		6.4		8.5		ns
t _{EABWP}	2.7		3.5		4.7		ns
t _{EABWCOMB}	5.9		7.7		10.3		ns
t _{EABWCREG}	5.4		7.0		9.4		ns
t _{EABDD}		3.4		4.5		5.9	ns
t _{EABDATACO}		0.5		0.7		0.8	ns
t _{EABDATASU}	0.8		1.0		1.4		ns
t _{EABDATAH}	0.1		0.1		0.2		ns
t _{EABWESU}	1.1		1.4		1.9		ns
t _{EABWEH}	0.0		0.0		0.0		ns
t _{EABWDSU}	1.0		1.3		1.7		ns
t _{EABWDH}	0.2		0.2		0.3		ns
t _{EABWASU}	4.1		5.1		6.8		ns
t _{EABWAH}	0.0		0.0		0.0		ns
t _{EABWO}		3.4		4.5		5.9	ns

Table 62. EPF10	K200E Device	(200E Device EAB Internal Timing Macroparameters (Part 2 of 2) Note (1)							
Symbol	-1 Spee	-1 Speed Grade		-2 Speed Grade		ed Grade	Unit		
	Min	Max	Min	Max	Min	Max			
t _{EABWCOMB}	6.7		8.1		10.7		ns		
t _{EABWCREG}	6.6		8.0		10.6		ns		
t _{EABDD}		4.0		5.1		6.7	ns		
t _{EABDATACO}		0.8		1.0		1.3	ns		
t _{EABDATASU}	1.3		1.6		2.1		ns		
t _{EABDATAH}	0.0		0.0		0.0		ns		
t _{EABWESU}	0.9		1.1		1.5		ns		
t _{EABWEH}	0.4		0.5		0.6		ns		
t _{EABWDSU}	1.5		1.8		2.4		ns		
t _{EABWDH}	0.0		0.0		0.0		ns		
t _{EABWASU}	3.0		3.6		4.7		ns		
t _{EABWAH}	0.4		0.5		0.7		ns		
t _{EABWO}		3.4		4.4		5.8	ns		

Table 63. EPF10k	K200E Device	e Interconne	ct Timing M	icroparame	ters Not	e (1)	
Symbol	-1 Spec	ed Grade	-2 Spee	d Grade	-3 Spee	d Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{DIN2IOE}		4.2		4.6		5.7	ns
t _{DIN2LE}		1.7		1.7		2.0	ns
t _{DIN2DATA}		1.9		2.1		3.0	ns
t _{DCLK2IOE}		2.5		2.9		4.0	ns
t _{DCLK2LE}		1.7		1.7		2.0	ns
t _{SAMELAB}		0.1		0.1		0.2	ns
t _{SAMEROW}		2.3		2.6		3.6	ns
t _{SAMECOLUMN}		2.5		2.7		4.1	ns
t _{DIFFROW}		4.8		5.3		7.7	ns
t _{TWOROWS}		7.1		7.9		11.3	ns
t _{LEPERIPH}		7.0		7.6		9.0	ns
t _{LABCARRY}		0.1		0.1		0.2	ns
t _{LABCASC}		0.9		1.0		1.4	ns

Symbol	-1 Spec	-1 Speed Grade		-2 Speed Grade		d Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{DRR}		8.0		9.5		12.5	ns
t _{INSU} (2)	2.4		2.9		3.9		ns
t _{INH} (2)	0.0		0.0		0.0		ns
t _{оитсо} (2)	2.0	4.3	2.0	5.2	2.0	7.3	ns
t _{INSU} (3)	2.4		2.9				ns
t _{INH} (3)	0.0		0.0				ns
t _{оитсо} (3)	0.5	3.3	0.5	4.1			ns
t _{PCISU}	2.4		2.9		_		ns
t _{PCIH}	0.0		0.0		_		ns
t _{PCICO}	2.0	6.0	2.0	7.7	_	-	ns

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSUBIDIR} (2)	2.7		3.2		4.3		ns
t _{INHBIDIR} (2)	0.0		0.0		0.0		ns
t _{INHBIDIR} (3)	0.0		0.0		-		ns
t _{INSUBIDIR} (3)	3.7		4.2		-		ns
toutcobidir (2)	2.0	4.5	2.0	5.2	2.0	7.3	ns
t _{XZBIDIR} (2)		6.8		7.8		10.1	ns
t _{ZXBIDIR} (2)		6.8		7.8		10.1	ns
toutcobidir (3)	0.5	3.5	0.5	4.2	-	-	
xzbidir (3)		6.8		8.4		-	ns
t _{ZXBIDIR} (3)		6.8		8.4		_	ns

Notes to tables:

- All timing parameters are described in Tables 24 through 30. This parameter is measured without use of the ClockLock or ClockBoost circuits.
- This parameter is measured with use of the ClockLock or ClockBoost circuits (3)

Power Consumption

The supply power (P) for FLEX 10KE devices can be calculated with the following equation:

$$P = P_{INT} + P_{IO} = (I_{CCSTANDBY} + I_{CCACTIVE}) \times V_{CC} + P_{IO}$$

The $I_{CCACTIVE}$ value depends on the switching frequency and the application logic. This value is calculated based on the amount of current that each LE typically consumes. The P_{IO} value, which depends on the device output load characteristics and switching frequency, can be calculated using the guidelines given in *Application Note 74 (Evaluating Power for Altera Devices)*.

Compared to the rest of the device, the embedded array consumes a negligible amount of power. Therefore, the embedded array can be ignored when calculating supply current.

The I_{CCACTIVE} value can be calculated with the following equation:

$$I_{CCACTIVE} = K \times f_{\boldsymbol{MAX}} \times N \times \boldsymbol{tog_{LC}} \times \frac{\mu A}{MHz \times LE}$$

Where:

f_{MAX} = Maximum operating frequency in MHz N = Total number of LEs used in the device

togLC = Average percent of LEs toggling at each clock

(typically 12.5%)

K = Constant

Table 80 provides the constant (K) values for FLEX 10KE devices.

Table 80. FLEX 10KE K Constant Values					
Device	K Value				
EPF10K30E	4.5				
EPF10K50E	4.8				
EPF10K50S	4.5				
EPF10K100E	4.5				
EPF10K130E	4.6				
EPF10K200E	4.8				
EPF10K200S	4.6				

This calculation provides an I_{CC} estimate based on typical conditions with no output load. The actual I_{CC} should be verified during operation because this measurement is sensitive to the actual pattern in the device and the environmental operating conditions.



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